

Abstract

A method of polishing a surface (120) of an article, e.g., a semiconductor wafer (112, 212), using a polishing layer (108, 208) in the presence of a polishing medium, such as a slurry (116). The method includes selecting the rotational rate of the article or the velocity of the polishing layer, or both, so as to control either removal rate uniformity or the occurrence of defects on the polished surface, or both.